

ABSTRACT OF THE DISCLOSURE

A chemical vapor deposition apparatus includes a deposition chamber defined at least in part by at least one of a chamber sidewall and a chamber base wall. A substrate holder is received within the chamber. At least one process chemical inlet to the deposition chamber is included. At least one of the chamber sidewall and chamber base wall includes a chamber surface having a plurality of purge gas inlets to the chamber therein. The purge gas inlets are separate from the at least one process chemical inlet. A purge gas inlet passageway is provided in fluid communication with the purge gas inlets. Further implementations, including deposition method implementations, are contemplated.